

VCSEL

KODENSHI

KVCB1-8512

VCSEL, or Vertical Cavity Surface Emitting Laser, is semiconductor microlaser diode that emits light in a cylindrical beam vertically from the surface of a fabricated wafer.

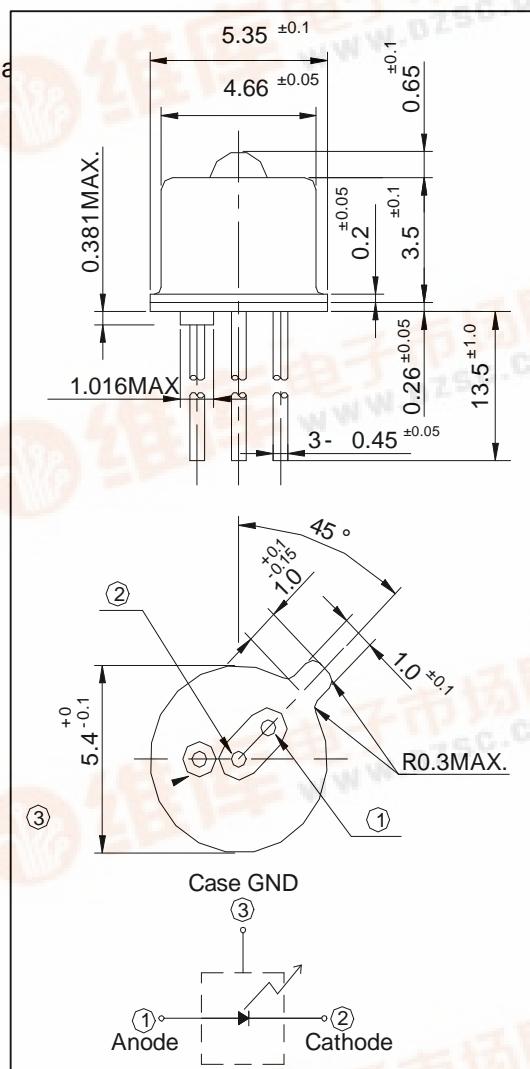
FEATURES

- 850nm wavelength range
- High data rate 2.5Gbps
- High reliability
- Low current and voltage
- Other configurations available on request

APPLICATIONS

- Fiber optic data links
- Proximity Sensors
- Encoders
- Laser range finders
- Laser printing
- Bar code scanning
- Optical storage

DIMENSIONS Unit:(mm)

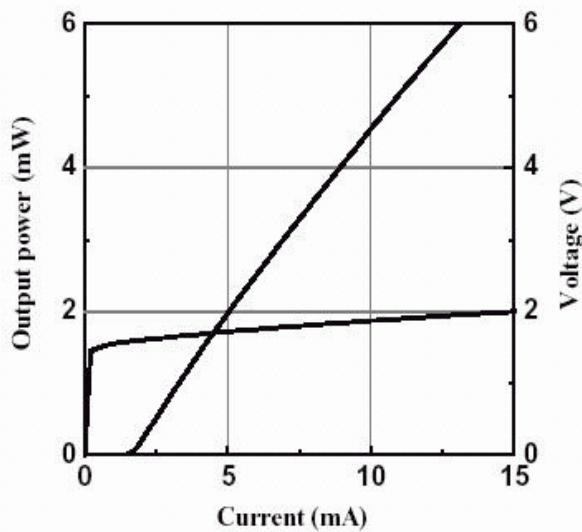


ABSOLUTE MAXIMUM RATINGS

Item	Symbol	Ratings	Unit
Operating Temperature	T _{opr.}	0 ~ +70	
Storage Temperature	T _{std.}	-40 ~ +100	
Lead Solder Temperature (10sec)	T _{sol}	260	
Continuous Forward Current	I _F	10	mA
Continuous Reverse Voltage	V _R	5	V

KVCB1-8512**ELECTRO-OPTICAL CHARACTERISTICS**

Parameter	Symbol	Min	Typ	Max	Unit	Test Conditions
Threshold Current	I_{th}		1.5	3	mA	CW
I_{th} Temperature Variation	I_{th}		1		mA	$T_a=0$ to 70
Slope Efficiency		0.3	0.5	0.7	mW/mA	$I_F=6\text{mA}$
Temperature Coefficient	/ T		-0.5		%/	$T_a=0$ to 70 at 6mA
Optical Output Power	P_o		2.5		mW	$I_F=6\text{mA}$
Peak Wavelength	λ_p	840	850	860	nm	$I_F=6\text{mA}$
λ_p Temperature Coefficient	λ_p / T		0.06		nm/	$T_a=0$ to 70 at 6mA
Spectral Bandwidth			0.5	0.85	nm	$I_F=6\text{mA}$
Beam Divergence		5	10	15	°	$P_o=1.5\text{mW}$, Full Width, $1/e^2$
Forward Voltage	V_f		1.8	2.2	V	$I_F=6\text{mA}$
Breakdown Voltage	V_b		-10		V	
Dynamic Resistance	R_d	25	35	55		$I_F=6\text{mA}$

L-I-V Curve2.5Gbps Eye Diagram